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2N3905



PNP General Purpose Amplifier

This device is designed for use as general purpose amplifiers and switches requiring collector currents to 100 mA.

Absolute Maximum Ratings*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{CEO}	Collector-Emitter Voltage	40	V
V _{CBO}	Collector-Base Voltage	40	V
V _{EBO}	Emitter-Base Voltage	5.0	V
I _C	Collector Current - Continuous	200	mA
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

^{*}These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.

2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		2N3905	
P _D	Total Device Dissipation Derate above 25°C	625 5.0	mW mW/°C
R _{θJC}	Thermal Resistance, Junction to Case	83.3	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	°C/W

PNP General Purpose Amplifier (continued)

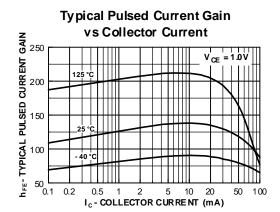
Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHA	RACTERISTICS				
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage*	$I_{\rm C} = 1.0 \text{ mA}, I_{\rm B} = 0$	40		V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_{C} = 10 \mu\text{A}, I_{E} = 0$	40		V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_E = 10 \mu\text{A}, I_C = 0$	5.0		V
CEX	Collector Cutoff Current	$V_{CE} = 30 \text{ V}, V_{OB} = 3.0 \text{ V}$	0.0	50	nA
BL	Base Cutoff Current	$V_{CE} = 30 \text{ V}, V_{OB} = 3.0 \text{ V}$		50	nA
ON CHAR	RACTERISTICS*	$V_{CE} = 1.0 \text{ V}, I_{C} = 0.1 \text{ mA}$	30		ı
IFE	De Culien Gain	$V_{CE} = 1.0 \text{ V}, I_{C} = 0.1 \text{ mA}$ $V_{CE} = 1.0 \text{ V}, I_{C} = 1.0 \text{ mA}$ $V_{CE} = 1.0 \text{ V}, I_{C} = 10 \text{ mA}$ $V_{CE} = 1.0 \text{ V}, I_{C} = 50 \text{ mA}$ $V_{CE} = 1.0 \text{ V}, I_{C} = 100 \text{ mA}$	40 50 30 15	150	
√ _{CE(sat)}	Collector-Emitter Saturation Voltage	$I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$ $I_C = 50 \text{ mA}, I_B = 5.0 \text{ mA}$		0.25 0.40	V V
V _{BE(sat)}	Base-Emitter Saturation Voltage	$I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$ $I_C = 50 \text{ mA}, I_B = 5.0 \text{ mA}$	0.65	0.85 0.95	V V
SMALL S	IGNAL CHARACTERISTICS	$I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$ $I_C = 50 \text{ mA}, I_B = 5.0 \text{ mA}$	0.65		V
SMALL S	IGNAL CHARACTERISTICS Output Capacitance	$I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$ $I_C = 50 \text{ mA}, I_B = 5.0 \text{ mA}$ $V_{CB} = 5.0 \text{ V}, f = 1.0 \text{ MHz}$	0.65	0.95 4.5	V V
SMALL S	IGNAL CHARACTERISTICS	$I_{C} = 10 \text{ mA}, I_{B} = 1.0 \text{ mA}$ $I_{C} = 50 \text{ mA}, I_{B} = 5.0 \text{ mA}$ $V_{CB} = 5.0 \text{ V}, f = 1.0 \text{ MHz}$ $V_{EB} = 0.5 \text{ V}, f = 1.0 \text{ MHz}$ $I_{C} = 10 \text{ mA}, V_{CE} = 20 \text{ V},$	2.0	0.95	V
SMALL S	IGNAL CHARACTERISTICS Output Capacitance Input Capacitance	$\begin{split} I_C &= 10 \text{ mA, } I_B = 1.0 \text{ mA} \\ I_C &= 50 \text{ mA, } I_B = 5.0 \text{ mA} \\ \end{split}$ $\begin{split} V_{CB} &= 5.0 \text{ V, } f = 1.0 \text{ MHz} \\ V_{EB} &= 0.5 \text{ V, } f = 1.0 \text{ MHz} \\ \end{split}$ $\begin{split} I_C &= 10 \text{ mA, } V_{CE} = 20 \text{ V, } f = 100 \text{ MHz} \end{split}$		0.95 4.5	V V
SMALL S	IGNAL CHARACTERISTICS Output Capacitance Input Capacitance Small-Signal Current Gain	$I_{C} = 10 \text{ mA}, I_{B} = 1.0 \text{ mA}$ $I_{C} = 50 \text{ mA}, I_{B} = 5.0 \text{ mA}$ $V_{CB} = 5.0 \text{ V}, f = 1.0 \text{ MHz}$ $V_{EB} = 0.5 \text{ V}, f = 1.0 \text{ MHz}$ $I_{C} = 10 \text{ mA}, V_{CE} = 20 \text{ V},$	2.0	0.95 4.5 10	V V pF pF
SMALL S Cob Cib Offe	IGNAL CHARACTERISTICS Output Capacitance Input Capacitance Small-Signal Current Gain Small-Signal Current Gain	$\begin{split} I_C &= 10 \text{ mA, } I_B = 1.0 \text{ mA} \\ I_C &= 50 \text{ mA, } I_B = 5.0 \text{ mA} \\ \end{split}$ $\begin{split} V_{CB} &= 5.0 \text{ V, } f = 1.0 \text{ MHz} \\ V_{EB} &= 0.5 \text{ V, } f = 1.0 \text{ MHz} \\ I_C &= 10 \text{ mA, } V_{CE} = 20 \text{ V, } \\ f &= 100 \text{ MHz} \\ I_C &= 1.0 \text{ mA, } V_{CE} = 10 \text{ V, } \end{split}$	2.0	0.95 4.5 10 200	V V
SMALL S Cob Cib Offe Ore	IGNAL CHARACTERISTICS Output Capacitance Input Capacitance Small-Signal Current Gain Small-Signal Current Gain Voltage Feedback Ratio	$\begin{split} I_C &= 10 \text{ mA, } I_B = 1.0 \text{ mA} \\ I_C &= 50 \text{ mA, } I_B = 5.0 \text{ mA} \\ \end{split}$ $\begin{split} V_{CB} &= 5.0 \text{ V, } f = 1.0 \text{ MHz} \\ V_{EB} &= 0.5 \text{ V, } f = 1.0 \text{ MHz} \\ I_C &= 10 \text{ mA, } V_{CE} = 20 \text{ V, } \\ f &= 100 \text{ MHz} \\ I_C &= 1.0 \text{ mA, } V_{CE} = 10 \text{ V, } \end{split}$	2.0 50 0.1	0.95 4.5 10 200 5.0	V V PF PF x10 ⁻⁴ kΩ
SMALL S Cob Cib Ofe Ore	IGNAL CHARACTERISTICS Output Capacitance Input Capacitance Small-Signal Current Gain Small-Signal Current Gain Voltage Feedback Ratio Input Impedance	$\begin{split} I_C &= 10 \text{ mA, } I_B = 1.0 \text{ mA} \\ I_C &= 50 \text{ mA, } I_B = 5.0 \text{ mA} \\ \end{split}$ $\begin{split} V_{CB} &= 5.0 \text{ V, } f = 1.0 \text{ MHz} \\ V_{EB} &= 0.5 \text{ V, } f = 1.0 \text{ MHz} \\ I_C &= 10 \text{ mA, } V_{CE} = 20 \text{ V, } \\ f &= 100 \text{ MHz} \\ I_C &= 1.0 \text{ mA, } V_{CE} = 10 \text{ V, } \end{split}$	2.0 50 0.1 0.5	0.95 4.5 10 200 5.0 8.0	V V PF pF x10 ⁻⁴ kΩ
SMALL S Cob Cib Ofe Ofe Ore No	IGNAL CHARACTERISTICS Output Capacitance Input Capacitance Small-Signal Current Gain Small-Signal Current Gain Voltage Feedback Ratio Input Impedance Output Impedance	$\begin{split} I_C &= 10 \text{ mA, } I_B = 1.0 \text{ mA} \\ I_C &= 50 \text{ mA, } I_B = 5.0 \text{ mA} \\ \end{split}$ $\begin{split} V_{CB} &= 5.0 \text{ V, } f = 1.0 \text{ MHz} \\ V_{EB} &= 0.5 \text{ V, } f = 1.0 \text{ MHz} \\ I_C &= 10 \text{ mA, } V_{CE} = 20 \text{ V, } \\ f &= 100 \text{ MHz} \\ \end{split}$ $\begin{split} I_C &= 1.0 \text{ mA, } V_{CE} = 10 \text{ V, } \\ f &= 1.0 \text{ KHz} \\ \end{split}$ $V_{CE} &= 5.0 \text{ V, } I_C = 100 \mu\text{A, } \\ R_S &= 1.0 k\Omega, \end{split}$	2.0 50 0.1 0.5	0.95 4.5 10 200 5.0 8.0 40	PF pF x10 ⁻⁴ kΩ μmhos
SMALL S Cob Cib Ofe Ofe Noe NF	IGNAL CHARACTERISTICS Output Capacitance Input Capacitance Small-Signal Current Gain Small-Signal Current Gain Voltage Feedback Ratio Input Impedance Output Impedance Noise Figure	$\begin{split} I_C &= 10 \text{ mA, } I_B = 1.0 \text{ mA} \\ I_C &= 50 \text{ mA, } I_B = 5.0 \text{ mA} \\ \end{split}$ $\begin{split} V_{CB} &= 5.0 \text{ V, } f = 1.0 \text{ MHz} \\ V_{EB} &= 0.5 \text{ V, } f = 1.0 \text{ MHz} \\ I_C &= 10 \text{ mA, } V_{CE} = 20 \text{ V, } \\ f &= 100 \text{ MHz} \\ \end{split}$ $\begin{split} I_C &= 1.0 \text{ mA, } V_{CE} = 10 \text{ V, } \\ f &= 1.0 \text{ KHz} \\ \end{split}$ $V_{CE} &= 5.0 \text{ V, } I_C = 100 \mu\text{A, } \\ R_S &= 1.0 k\Omega, \end{split}$	2.0 50 0.1 0.5	0.95 4.5 10 200 5.0 8.0 40	PF pF x10 ⁻⁴ kΩ μmhos
SMALL S Cob Crib Offe Offe Ooe NF	IGNAL CHARACTERISTICS Output Capacitance Input Capacitance Small-Signal Current Gain Small-Signal Current Gain Voltage Feedback Ratio Input Impedance Output Impedance Noise Figure NG CHARACTERISTICS	$\begin{split} &I_C = 10 \text{ mA, } I_B = 1.0 \text{ mA} \\ &I_C = 50 \text{ mA, } I_B = 5.0 \text{ mA} \\ \end{split}$ $&V_{CB} = 5.0 \text{ V, } f = 1.0 \text{ MHz} \\ &V_{EB} = 0.5 \text{ V, } f = 1.0 \text{ MHz} \\ &I_C = 10 \text{ mA, } V_{CE} = 20 \text{ V, } \\ &f = 100 \text{ MHz} \\ &I_C = 1.0 \text{ mA, } V_{CE} = 10 \text{ V, } \\ &f = 1.0 \text{ KHz} \\ \end{split}$ $&V_{CE} = 5.0 \text{ V, } I_C = 100 \mu\text{A, } \\ &R_S = 1.0 k\Omega, \\ &R_W = 10 \text{ Hz to } 15.7 \text{ KHz} \\ \end{split}$ $&V_{CC} = 3.0 \text{ V, } I_{CS} = 10 \text{ mA, } \\ &I_{B1} = 1.0 \text{ mA, } V_{OB \text{ (off)}} = 3.0 \text{ V} \end{split}$	2.0 50 0.1 0.5	0.95 4.5 10 200 5.0 8.0 40 5.0	PF PF pF x10 ⁻⁴ kΩ μmhos dB
SMALL S Cob Cib Ofe Ofe One	IGNAL CHARACTERISTICS Output Capacitance Input Capacitance Small-Signal Current Gain Small-Signal Current Gain Voltage Feedback Ratio Input Impedance Output Impedance Noise Figure NG CHARACTERISTICS Delay Time	$\begin{split} &I_C = 10 \text{ mA, } I_B = 1.0 \text{ mA} \\ &I_C = 50 \text{ mA, } I_B = 5.0 \text{ mA} \\ \end{split}$ $&V_{CB} = 5.0 \text{ V, } f = 1.0 \text{ MHz} \\ &V_{EB} = 0.5 \text{ V, } f = 1.0 \text{ MHz} \\ &I_C = 10 \text{ mA, } V_{CE} = 20 \text{ V, } \\ &f = 100 \text{ MHz} \\ &I_C = 1.0 \text{ mA, } V_{CE} = 10 \text{ V, } \\ &f = 1.0 \text{ KHz} \\ \end{split}$ $&V_{CE} = 5.0 \text{ V, } I_C = 100 \mu\text{A, } \\ &R_S = 1.0 k\Omega, \\ &R_W = 10 \text{ Hz to } 15.7 \text{ KHz} \\ \end{split}$	2.0 50 0.1 0.5	0.95 4.5 10 200 5.0 8.0 40 5.0	PF pF x10 ⁻⁴ kΩ μmhos dB

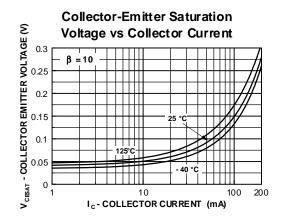
^{*}Pulse Test: Pulse Width ≤300 μs, Duty Cycle ≤2.0%

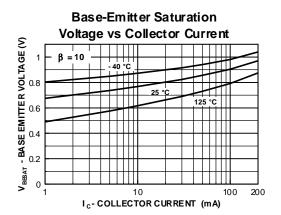
PNP General Purpose Amplifier

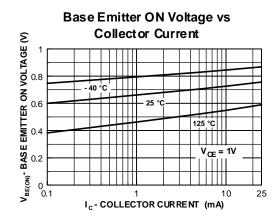
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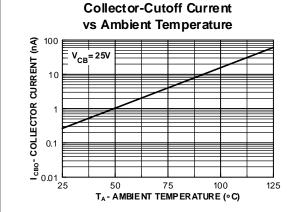
Typical Characteristics

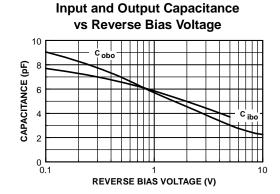










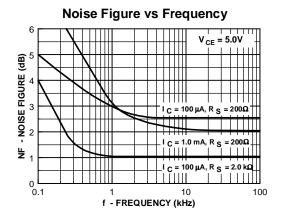


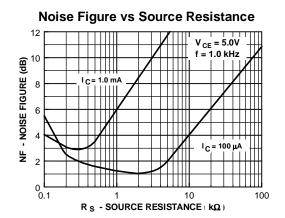
Common-Base Open Circuit

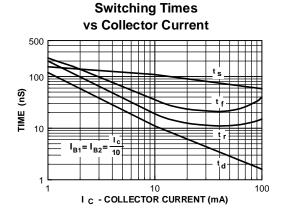
PNP General Purpose Amplifier

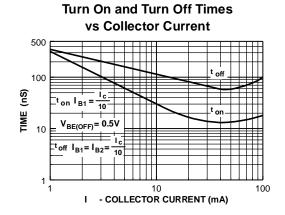
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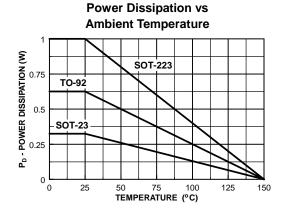
Typical Characteristics (continued)







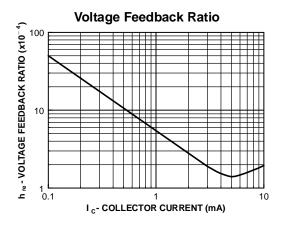


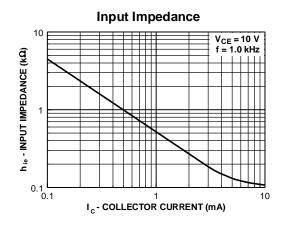


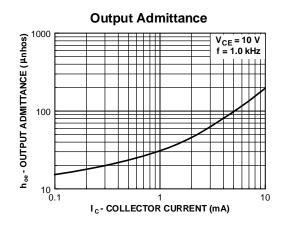
PNP General Purpose Amplifier

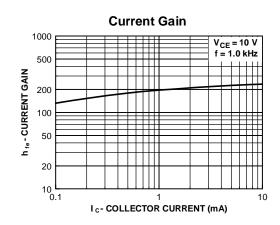
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Typical Characteristics (continued)









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